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APPLICATION NO. FILING DATE		ILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
09/387,477	09/387,477 09/01/1999		Manabu Tomita	TIJ-26105	2630	
23494	7590	03/11/2005		EXAMINER		
TEXAS IN	STRUM	ENTS INCORPO	GUERRERO, MARIA F			
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DALLAS, 7	ΓX 7526	5		ART UNIT	PAPER NUMBER	
				2822		
				DATE MAILED: 03/11/2005		

Please find below and/or attached an Office communication concerning this application or proceeding.

	,	Application No.	Applicant(s)	
		09/387,477	TOMITA ET AL.	
	Office Action Summary	Examiner	Art Unit	
		Maria Guerrero	2822	
Period f	The MAILING DATE of this communication Reply	on appears on the cover sheet wi	th the correspondence address -	-
THE - Extended - If th - If No - Fail Any	HORTENED STATUTORY PERIOD FOR I MAILING DATE OF THIS COMMUNICAT ensions of time may be available under the provisions of 37 r SIX (6) MONTHS from the mailing date of this communica e period for reply specified above is less than thirty (30) day 0 period for reply is specified above, the maximum statutory ure to reply with in the set or extended period for reply will, b reply received by the Office later than three months after the patent term adjustment. See 37 CFR 1.704(b).	FION.  CFR 1.136(a). In no event, however, may a retion.  s, a reply within the statutory minimum of thirt period will apply and will expire SIX (6) MON y statute, cause the application to become AB	eply be timely filed ty (30) days will be considered timely. THS from the mailing date of this communical BANDONED (35 U.S.C. § 133).	· ition.
Status				
1)⊠	Responsive to communication(s) filed or	n <u>06 December 2004</u> .		
2a)⊠	This action is <b>FINAL</b> . 2b)	This action is non-final.		
3)□	Since this application is in condition for a closed in accordance with the practice up	•	• •	is
Disposit	ion of Claims			
4)⊠ 5)□ 6)⊠ 7)□ 8)□	· / <del></del>	ithdrawn from consideration.		
Applicat	ion Papers			
9)[	The specification is objected to by the Ex	aminer.		
10)	The drawing(s) filed on is/are: a)	☐ accepted or b)☐ objected to	by the Examiner.	-
	Applicant may not request that any objection	- · ·	` '	
	Replacement drawing sheet(s) including the	· · · · · · · · · · · · · · · · · · ·	'	• •
11)[	The oath or declaration is objected to by	the Examiner. Note the attached	Office Action or form PTO-152.	
Priority	under 35 U.S.C. § 119			
а)	Acknowledgment is made of a claim for for All b) Some * c) None of:  1. Certified copies of the priority docu 2. Certified copies of the priority docu 3. Copies of the certified copies of the application from the International Esee the attached detailed Office action for	uments have been received. uments have been received in A e priority documents have been Bureau (PCT Rule 17.2(a)).	pplication No received in this National Stage	
Attachmen	ut(s)			
	ce of References Cited (PTO-892)		ummary (PTO-413)	
3) 🔲 Infor	ce of Draftsperson's Patent Drawing Review (PTO-94 mation Disclosure Statement(s) (PTO-1449 or PTO/9 er No(s)/Mail Date		e)/Mail Date Iformal Patent Application (PTO-152) 	

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### **DETAILED ACTION**

1. This Office Action is in response to the amendment filed December 6, 2004.

### **Status of Claims**

2. Claims 2 and 8-9 are canceled. Claims 1 and 3-7 are pending.

# Claim Rejections - 35 USC § 112

The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

3. Claim 3 is rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Claim 3 recites "wherein C4F8 is used as the fluorocarbon gas having a lower ratio of carbon atoms to fluorine atoms and at least one selected from the group composed of CHF3, CH2F2 and CF4 is used as the fluorocarbon gas having higher ratio of carbon atoms to fluorine atoms". The claim is vague and indefinite because the specification describes C4F8 as the fluorocarbon gas having the higher ratio of carbon atoms to fluorine atoms and CHF3, CH2F2 and CF4 as the fluorocarbon gas having the lower ratio of carbon atoms to fluorine atoms (page 4, page 6, lines 1-10, page 7, lines 9-27). In addition, original claim 3 described C4F8 as the fluorocarbon gas having the higher ratio of carbon atoms to fluorine atoms and CHF3, CH2F2 and CF4 as the fluorocarbon gas having the lower ratio of carbon atoms to fluorine atoms to fluorine atoms.

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## Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- (e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.
- 4. Claims 1 and 4 are rejected under 35 U.S.C. 102(b) as being anticipated by Yanagida (U.S. 5,338,399).

Yanagida teaches providing a semiconductor substrate having a lower electrically conducting layer (2) thereon and an electrically insulating layer (3) disposed over the electrically conducting layer (2) (Fig. 1a, col. 8, lines 15-20). Yanagida shows providing a gas etchant comprising a mixed gas of two different fluorocarbon gases, each fluorocarbon gas having a different ratio of carbon atoms to fluorine atoms that have different ratios of carbon atoms to fluorine atoms (col. 11, lines 5-20, 38-43). Yanagida discloses the fluorocarbon gas having the lower ratio of carbon atoms to fluorine atoms forming at least one half of the mixed gas (col. 11, lines 38-43). Yanagida teaches etching a connection hole through the electrically insulating layer in a single etching step to the electrically conducting layer using only the mixed gas as the etchant

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(Fig. 1b, col. 11, lines 5-20, 38-43). Yanagida shows the insulating layer being plasma etched with the mixed gas of fluorocarbon gases (col. 11, lines 60-62).

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5. Claim 1 is rejected under 35 U.S.C. 102(e) as being anticipated by Nguyen et al. (U.S. 6,001,699).

Nguyen et al. teaches providing a semiconductor substrate having a lower electrically conducting layer thereon and an electrically insulating layer disposed over the electrically conducting layer (Fig. 2B-2C, Abstract, col. 5, lines 5-20, col. 6, lines 1-45). Nguyen et al. shows providing a gas etchant comprising a mixed gas of two different fluorocarbon gases, each fluorocarbon gas having a different ratio of carbon atoms to fluorine atoms that have different ratios of carbon atoms to fluorine atoms (Abstract, col. 5, lines 64-67). Nguyen et al. discloses the fluorocarbon gas having the higher ratio of carbon atoms to fluorine atoms forming at least one half of the mixed gas (Abstract, col. 5, lines 64-67, col. 8, lines 1-3). Nguyen et al. teaches etching a connection hole through the electrically insulating layer in a single etching step to the electrically conducting layer using only the mixed gas as the etchant (Fig. 2B-2C, col. 7, lines 20-40).

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### Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

- (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 6. Claims 5-7 are rejected under 35 U.S.C. 103(a) as being unpatentable over Yanagida (U.S. 5,338,399) in view of Mizuhara et al. (U.S. 5,898,221).

Regarding claims 5-7, Yanagida does not specifically show the upper electrically conducting layer (electrode or wiring) connected to the lower electrically conducting layer. Yanagida does not specifically show the lower conducting layer having a titanium nitride layer, a layer of aluminum, a titanium layer and a titanium nitride layer stacked in that order. Yanagida does not specifically show the electrically insulating having the silicon oxide layer formed from TEOS, the spin-on glass layer, and the silicon oxide formed from TEOS stacked in that order. However, Mizuhara et al. shows the upper electrically conducting layer (electrode or wiring) connected to the lower electrically conducting layer (Fig. 9, col. 5, lines 5-9). Mizuhara et al. teaches the lower conducting layer having a titanium nitride layer, a layer of aluminum, a titanium layer and a titanium nitride layer stacked in that order (Fig. 3, 8-9, col. 3, lines 37-40). Mizuhara et al. discloses the electrically insulating having the silicon oxide layer formed from TEOS, the spin-on glass layer, and the silicon oxide formed from TEOS stacked in that order (Fig. 7-8, col. 4, lines 25-60).

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Therefore, it would have been obvious to a person of ordinary skill in the art at the time of the invention to modify Yanagida reference by including the specific configuration suggested by Mizuhara et al. in order to provide a multiplayer wiring structure having low pollution, low damage and improved reliability (Mizuhara et al., col. 1, lines 5-12; Yanagida, col. 3, lines 50-54).

### Response to Arguments

7. Applicant's arguments with respect to claims 1 and 4-7 have been considered but are most in view of the new ground(s) of rejection.

Applicant's arguments filed December 6, 2004 have been fully considered but they are not persuasive. The amendment to the specification does not overcome the 35 USC 112 rejection because the specification and the original claim 3 described C4F8 as the fluorocarbon gas having the higher ratio of carbon atoms to fluorine atoms and CHF3, CH2F2 and CF4 as the fluorocarbon gas having the lower ratio of carbon atoms to fluorine atoms (see original specification, page 4, page 6, lines 1-10, page 7, lines 9-27). The scope of the claim is uncertain because the specification as amended in page 3 describes C4F8, CHF2, and CF4 as gas with low C/F ratio. Clarification is requested.

#### Conclusion

8. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Kuroda (US 6,593,230) teaches using a gas etchant comprising a mixed gas of two different fluorocarbons C4F8 and CHF3 (col. 6, lines 45-50). Chung

(US 6,040,247) teaches using a gas etchant comprising a mixed gas of two different fluorocarbons CHF3 and CF4 (col. 5, lines 35-40).

9. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

10. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Maria Guerrero whose telephone number is 571-272-1837.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian can be reached on 571-272-1852. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

February 23, 2005

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